



# PJD15P06A-AU

## 60V P-Channel Enhancement Mode MOSFET

**Voltage**

**-60 V**

**Current**

**-15 A**

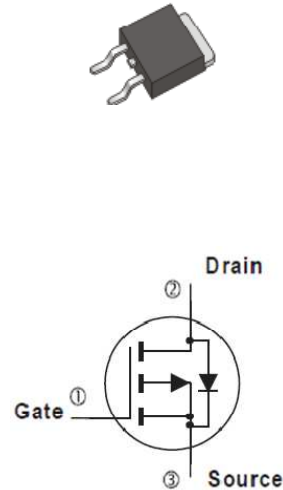
### Features

- $R_{DS(ON)}$ ,  $V_{GS}@-10V$ ,  $I_D@-7.5A < 68m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}@-4.5V$ ,  $I_D@-4A < 85m\Omega$
- High switching speed
- Improved dv/dt capability
- Low gate charge
- Low reverse transfer capacitance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

### Mechanical Data

- Case : TO-252AA Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.0105 ounces, 0.297grams

TO-252AA



### Maximum Ratings and Thermal Characteristics ( $T_A=25^\circ C$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		$V_{DS}$	-60	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	
Continuous Drain Current <sup>(Note 4)</sup>	$T_C=25^\circ C$	$I_D$	-15	A
	$T_C=100^\circ C$		-9.5	
Pulsed Drain Current <sup>(Note 1)</sup>	$T_C=25^\circ C$	$I_{DM}$	-60	
Power Dissipation	$T_C=25^\circ C$	$P_D$	25	W
	$T_C=100^\circ C$		10	
Continuous Drain Current <sup>(Note 4)</sup>	$T_A=25^\circ C$	$I_D$	-4	A
	$T_A=70^\circ C$		-3.2	
Power Dissipation	$T_A=25^\circ C$	$P_D$	2	W
	$T_A=70^\circ C$		1.3	
Single Pulse Avalanche Energy <sup>(Note 6)</sup>		$E_{AS}$	31	mJ
Operating Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~150	$^\circ C$
Typical Thermal Resistance <sup>(Note 4,5)</sup>	Junction to Case	$R_{\theta JC}$	5	$^\circ C/W$
	Junction to Ambient	$R_{\theta JA}$	62.5	

- Limited only By Maximum Junction Temperature



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## Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
<b>Static</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-60	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250uA	-1	-1.63	-2.5	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-7.5A	-	55	68	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4A	-	71	85	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-60V, V <sub>GS</sub> =0V	-	-	-1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
<b>Dynamic</b> (Note 7)						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-30V, I <sub>D</sub> =-7.5A, V <sub>GS</sub> =-10V (Note 3)	-	17	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	2.8	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	3.6	-	
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V, f=1MHZ	-	879	-	pF
Output Capacitance	C <sub>oss</sub>		-	70	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	47	-	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-30V, I <sub>D</sub> =-1A, V <sub>GS</sub> =-10V, R <sub>G</sub> =6Ω (Note 3)	-	8.4	-	ns
Turn-On Rise Time	t <sub>r</sub>		-	30	-	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	52	-	
Turn-Off Fall Time	t <sub>f</sub>		-	16	-	
<b>Drain-Source Diode</b>						
Maximum Continuous Drain-Source Diode Forward Current	I <sub>S</sub>	---	-	-	-15	A
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-1A, V <sub>GS</sub> =0V	-	-0.73	-1	V

**NOTES :**

- Pulse width ≤ 300us, Duty cycle ≤ 2%.
- Essentially independent of operating temperature typical characteristics.
- Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub> = 25°C.
- The maximum current rating is package limited.
- R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- L=0.1mH, I<sub>AS</sub>=-25A, V<sub>GS</sub>=-10V, V<sub>DS</sub>=-25V, R<sub>G</sub>=25 ohm.
- Guaranteed by design, not subject to production testing.



# PJD15P06A-AU

## TYPICAL CHARACTERISTIC CURVES

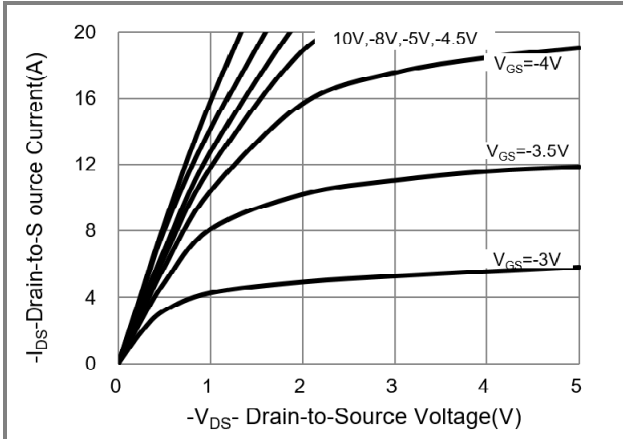


Fig.1 On-Region Characteristics

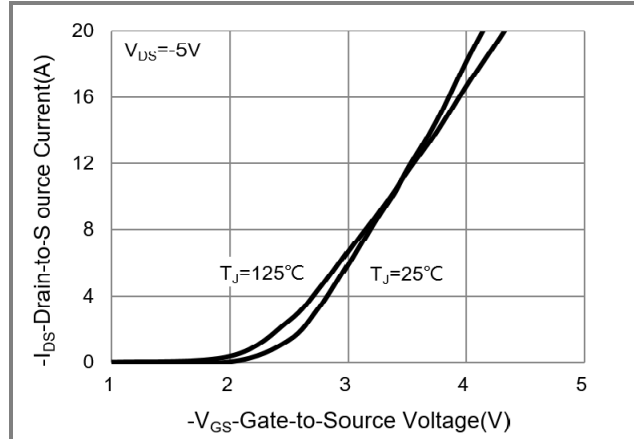


Fig.2 Transfer Characteristics

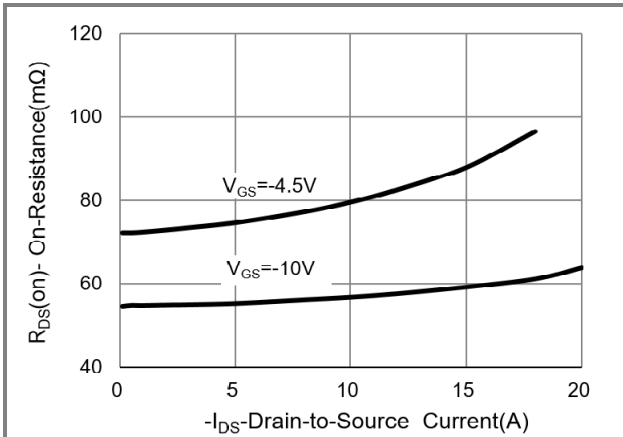


Fig.3 On-Resistance vs. Drain Current

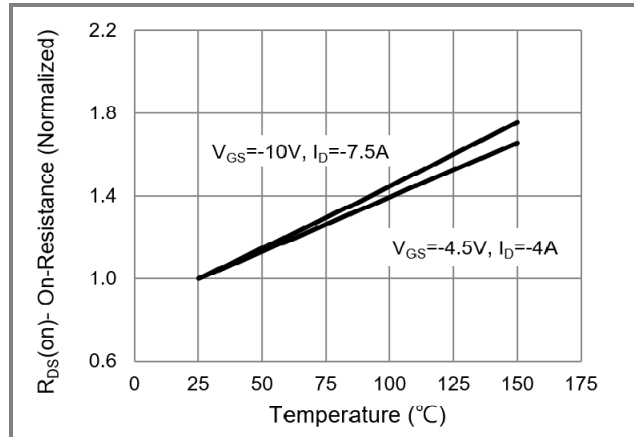


Fig.4 On-Resistance vs. Junction temperature

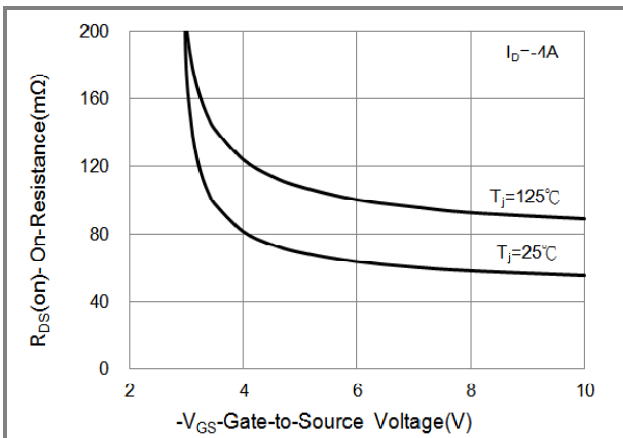


Fig.5 On-Resistance Variation with VGS

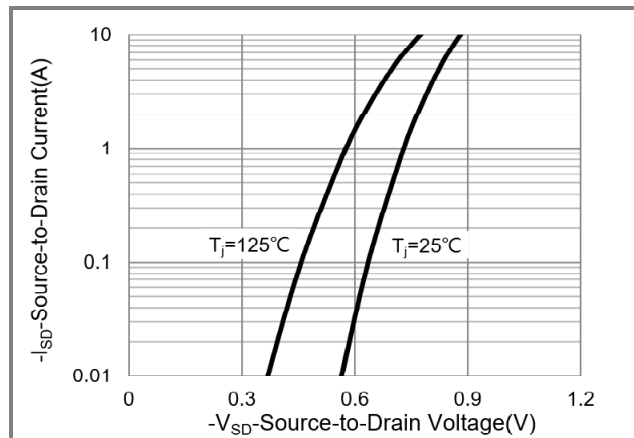


Fig.6 Body Diode Characteristics



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## TYPICAL CHARACTERISTIC CURVES

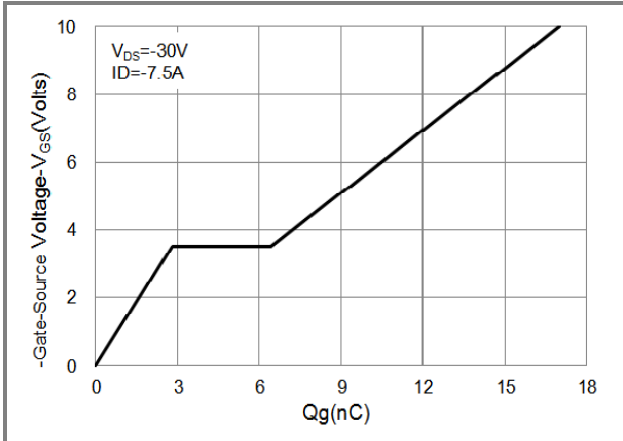


Fig.7 Gate-Charge Characteristics

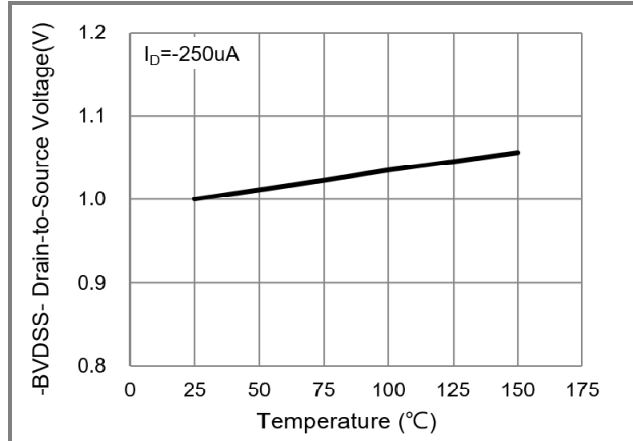


Fig.8 Breakdown Voltage Variation vs. Temperature

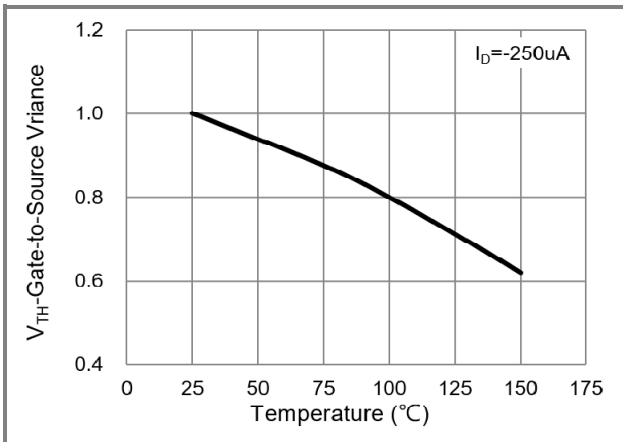


Fig.9 Threshold Voltage Variation with Temperature

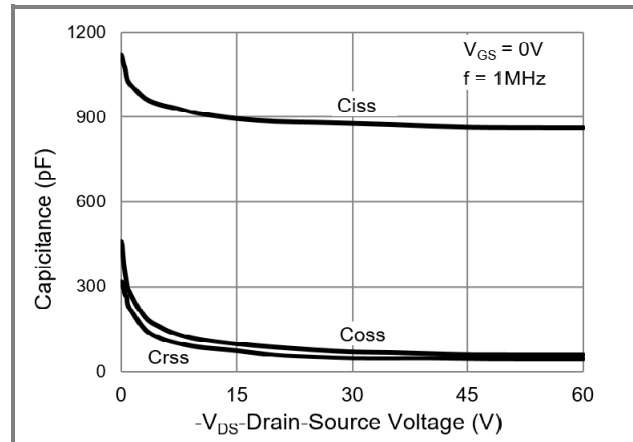


Fig.10 Capacitance vs. Drain-Source Voltage

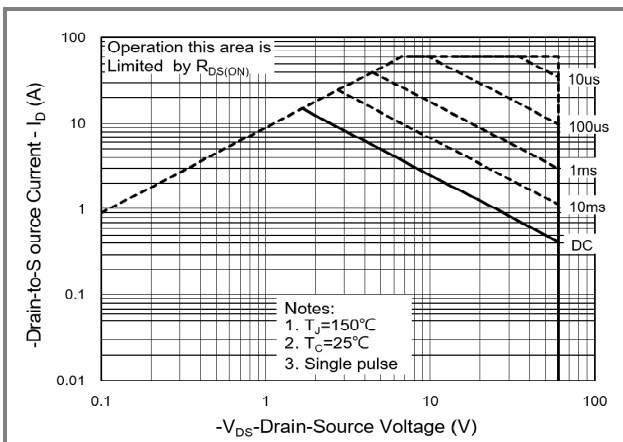


Fig.11 Maximum Safe Operating Area

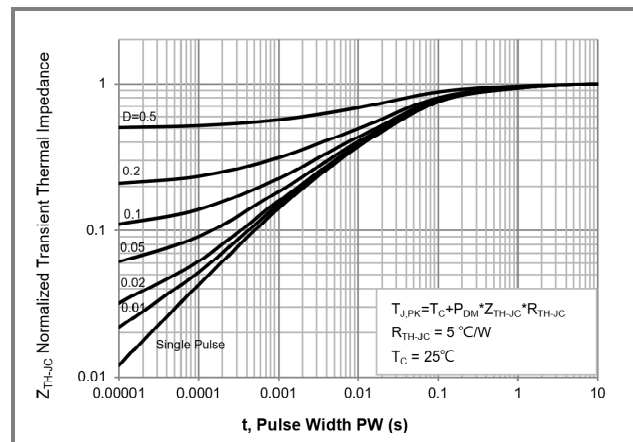


Fig.12 Normalized Thermal Transient Impedance



# PJD15P06A-AU

Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJD15P06A-AU_L2_000A1	TO-252AA	3,000pcs / 13" reel	D15P06A	Halogen free

## Packaging Information & Mounting Pad Layout

